Microsemi Corporation - M1AGLE3000V2-FGG896 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	75264
Total RAM Bits	516096
Number of I/O	620
Number of Gates	3000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1agle3000v2-fgg896

I/Os Per Package [1]

IGLOOe Devices	AGLE600		AGLE3000	
ARM-Enabled IGLOOe Devices			M1AGLE3000	
	I/O Types			
Package	Single-Ended I/O[1]	Differential I/O Pairs	Single-Ended I/O[1]	Differential I/O Pairs
FG256	165	79	–	–
FG484	270	135	341	168
FG896	–	–	620	310

Notes:

1. *When considering migrating your design to a lower- or higher-density device, refer to the* IGLOOe FPGA Fabric User's Guide *to ensure compliance with design and board migration requirements.*
2. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
3. *For AGLE3000 devices, the usage of certain I/O standards is limited as follows:*
   – SSTL3(I) and (II): up to 40 I/Os per north or south bank
   – LVPECL / GTL+ 3.3 V / GTL 3.3 V: up to 48 I/Os per north or south bank
   – SSTL2(I) and (II) / GTL+ 2.5 V/ GTL 2.5 V: up to 72 I/Os per north or south bank
4. *FG256 and FG484 are footprint-compatible packages.*
5. *When using voltage-referenced I/O standards, one I/O pin should be assigned as a voltage-referenced pin (VREF) per minibank (group of I/Os).*
6. *When the Flash*Freeze pin is used to directly enable Flash*Freeze mode and not as a regular I/O, the number of single-ended user I/Os available is reduced by one.*
7. *"G" indicates RoHS-compliant packages. Refer to* *"IGLOOe Ordering Information" on page III* *for the location of the "G" in the part number.*

IGLOOe FPGAs Package Sizes Dimensions

Package	FG256	FG484	FG896
Length × Width (mm × mm)	17 × 17	23 × 23	31 × 31
Nominal Area (mm2)	289	529	961
Pitch (mm)	1	1	1
Height (mm)	1.6	2.23	2.23

IGLOOe Device Status

IGLOOe Devices	Status	M1 IGLOOe Devices	Status
AGLE600	Production		
AGLE3000	Production	M1AGLE3000	Production

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, Flash-based IGLOOe devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOOe family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOOe family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOOe flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOOe FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOOe family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOOe family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOOe architecture provides granularity comparable to standard-cell ASICs. The IGLOOe device consists of five distinct and programmable architectural features (Figure 1-1 on page 4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- Pro I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOOe core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC® family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates. The absolute maximum junction temperature is 100°C. EQ 2 shows a sample calculation of the absolute maximum power dissipation allowed for an 896-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. } (°\text{C}) - \text{Max. ambient temp. } (°\text{C})}{\theta_{ja}(°\text{C/W})} = \frac{100°\text{C} - 70°\text{C}}{13.6°\text{C/W}} = 2.206\text{ W}$$

EQ 2

Table 2-5 • **Package Thermal Resistivities**

Package Type	Pin Count	θ_{jc}	θ_{ja} Still Air	θ_{ja} 200 ft./min.	θ_{ja} 500 ft./min.	Units
Plastic Quad Flat Package (PQFP)	208	8.0	26.1	22.5	20.8	C/W
Plastic Quad Flat Package (PQFP) with embedded heat spreader	208	3.8	16.2	13.3	11.9	C/W
Fine Pitch Ball Grid Array (FBGA)	256	3.8	26.9	22.8	21.5	C/W
	484	3.2	20.5	17.0	15.9	C/W
	676	3.2	16.4	13.0	12.0	C/W
	896	2.4	13.6	10.4	9.4	C/W

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C,VCC = 1.425 V) For IGLOOe V2 or V5 devices, 1.5 V DC Core Supply Voltage**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.945	0.965	0.978	1.000	1.008	1.013
1.500	0.876	0.893	0.906	0.927	0.934	0.940
1.575	0.824	0.840	0.852	0.872	0.879	0.884

Table 2-7 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.14 V) For IGLOOe V2, 1.2 V DC Core Supply Voltage**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.14	0.968	0.978	0.991	1.000	1.006	1.010
1.20	0.864	0.873	0.885	0.893	0.898	0.902
1.26	0.793	0.803	0.813	0.821	0.826	0.829

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-15.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-15.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-15. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

P_{STAT} = (PDC1 or PDC2 or PDC3) + N_{BANKS} * PDC5 + N_{INPUTS} * PDC6 + $N_{OUTPUTS}$ * P_{DC7}

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOOe FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOOe FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—P_{S-CELL}

$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-15.

F_{CLK} is the global clock signal frequency.

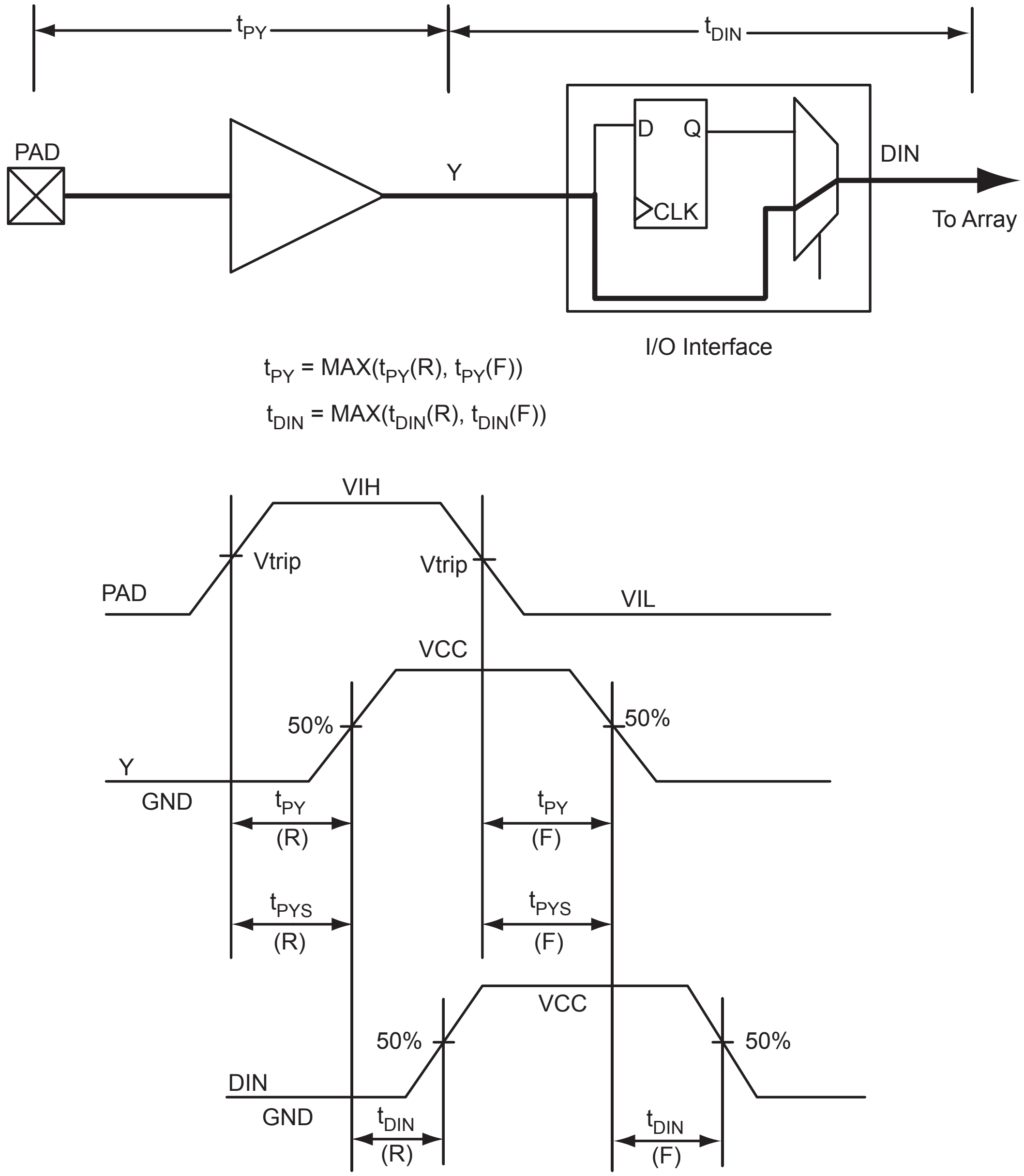

Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

Table 2-30 • I/O Short Currents IOSH/IOSL

	Drive Strength	IOSH (mA)*	IOSL (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	4 mA	25	27
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	4 mA	16	18
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCIX	Per PCI/PCI-X Specification	Per PCI Curves	
3.3 V GTL	25 mA	268	181
2.5 V GTL	25 mA	169	124
3.3 V GTL+	35 mA	268	181
2.5 V GTL+	33 mA	169	124
HSTL (I)	8 mA	32	39
HSTL (II)	15 mA	66	55
SSTL2 (I)	15 mA	83	87
SSTL2 (II)	18 mA	169	124
SSTL3 (I)	14 mA	51	54
SSTL3 (II)	21 mA	103	109

Note: $T_J = 100°C$

Timing Characteristics

1.5 V DC Core Voltage

Table 2-36 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.97	4.90	0.18	1.08	1.34	0.66	5.00	3.99	2.27	2.16	8.60	7.59	ns
8 mA	Std.	0.97	4.05	0.18	1.08	1.34	0.66	4.13	3.45	2.53	2.65	7.73	7.05	ns
12 mA	Std.	0.97	3.44	0.18	1.08	1.34	0.66	3.51	3.05	2.71	2.95	7.11	6.64	ns
16 mA	Std.	0.97	3.27	0.18	1.08	1.34	0.66	3.34	2.96	2.74	3.04	6.93	6.55	ns
24 mA	Std.	0.97	3.18	0.18	1.08	1.34	0.66	3.24	2.97	2.79	3.36	6.84	6.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-37 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.97	2.85	0.18	1.08	1.34	0.66	2.92	2.27	2.27	2.27	6.51	5.87	ns
8 mA	Std.	0.97	2.39	0.18	1.08	1.34	0.66	2.44	1.88	2.53	2.76	6.03	5.47	ns
12 mA	Std.	0.97	2.12	0.18	1.08	1.34	0.66	2.17	1.69	2.71	3.08	5.76	5.28	ns
16 mA	Std.	0.97	2.08	0.18	1.08	1.34	0.66	2.12	1.65	2.75	3.17	5.72	5.25	ns
24 mA	Std.	0.97	2.10	0.18	1.08	1.34	0.66	2.14	1.60	2.80	3.49	5.74	5.20	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-54 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	7.33	0.18	1.27	1.59	0.66	7.47	6.18	2.34	1.18	11.07	9.77	ns
4 mA	Std.	0.97	6.07	0.18	1.27	1.59	0.66	6.20	5.25	2.69	2.42	9.79	8.84	ns
6 mA	Std.	0.97	5.18	0.18	1.27	1.59	0.66	5.29	4.61	2.93	2.88	8.88	8.21	ns
8 mA	Std.	0.97	4.88	0.18	1.27	1.59	0.66	4.98	4.48	2.99	3.01	8.58	8.08	ns
12 mA	Std.	0.97	4.80	0.18	1.27	1.59	0.66	4.89	4.49	3.07	3.47	8.49	8.09	ns
16 mA	Std.	0.97	4.80	0.18	1.27	1.59	0.66	4.89	4.49	3.07	3.47	8.49	8.09	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-55 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.43	0.18	1.27	1.59	0.66	3.51	3.39	2.33	1.19	7.10	6.98	ns
4 mA	Std.	0.97	2.83	0.18	1.27	1.59	0.66	2.89	2.59	2.69	2.49	6.48	6.18	ns
6 mA	Std.	0.97	2.45	0.18	1.27	1.59	0.66	2.51	2.19	2.93	2.95	6.10	5.79	ns
8 mA	Std.	0.97	2.38	0.18	1.27	1.59	0.66	2.43	2.12	2.98	3.08	6.03	5.71	ns
12 mA	Std.	0.97	2.37	0.18	1.27	1.59	0.66	2.42	2.03	3.07	3.57	6.02	5.62	ns
16 mA	Std.	0.97	2.37	0.18	1.27	1.59	0.66	2.42	2.03	3.07	3.57	6.02	5.62	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-60 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	7.61	0.18	1.47	1.77	0.66	7.76	6.33	2.81	2.34	11.36	9.92	ns
4 mA	Std.	0.97	6.54	0.18	1.47	1.77	0.66	6.67	5.56	3.09	2.88	10.26	9.16	ns
6 mA	Std.	0.97	6.15	0.18	1.47	1.77	0.66	6.27	5.42	3.15	3.02	9.87	9.02	ns
8 mA	Std.	0.97	6.07	0.18	1.47	1.77	0.66	6.20	5.42	2.64	3.56	9.79	9.02	ns
12 mA	Std.	0.97	6.07	0.18	1.47	1.77	0.66	6.20	5.42	2.64	3.56	9.79	9.02	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-61 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.47	1.77	0.66	3.32	3.00	2.80	2.43	6.92	6.59	ns
4 mA	Std.	0.97	2.81	0.18	1.47	1.77	0.66	2.87	2.51	3.08	2.97	6.46	6.10	ns
6 mA	Std.	0.97	2.72	0.18	1.47	1.77	0.66	2.78	2.41	3.14	3.12	6.37	6.01	ns
8 mA	Std.	0.97	2.69	0.18	1.47	1.77	0.66	2.75	2.30	3.24	3.67	6.35	5.89	ns
12 mA	Std.	0.97	2.69	0.18	1.47	1.77	0.66	2.75	2.30	3.24	3.67	6.35	5.89	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-69 • **Minimum and Maximum DC Input and Output Levels**

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min., V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**µA[4]**	**µA[4]**
Per PCI specification	Per PCI curves										10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-12.

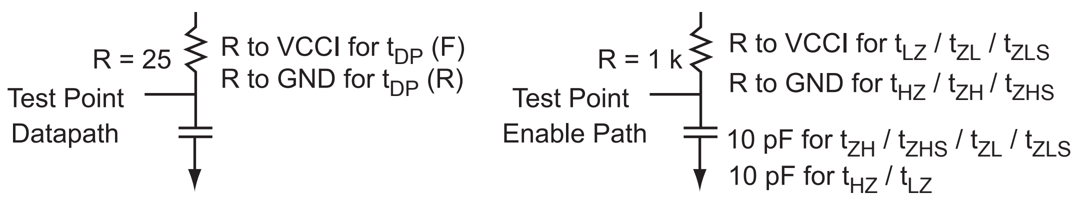

Figure 2-12 • **AC Loading**

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-70.

Table 2-70 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	–	10

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

HSTL Class I

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). IGLOOe devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-89 • Minimum and Maximum DC Input and Output Levels

HSTL Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
8 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8	32	39	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operating conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*

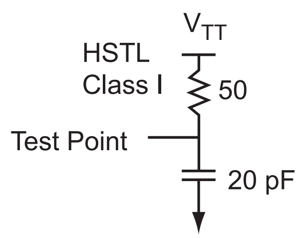

Figure 2-17 • AC Loading

Table 2-90 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-91 • HSTL Class I – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.98	2.74	0.19	1.77	0.67	2.79	2.73			6.42	6.36	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-92 • HSTL Class I – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	1.55	3.10	0.26	1.94	1.10	3.12	3.10			8.93	8.91	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). IGLOOe devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-93 • **Minimum and Maximum DC Input and Output Levels**

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
15 mA[5]	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15	66	55	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operating conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Output drive strength is below JEDEC specification.*

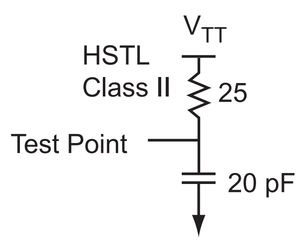

Figure 2-18 • **AC Loading**

Table 2-94 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-95 • **HSTL Class II – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.98	2.62	0.19	1.77	0.67	2.66	2.40			6.29	6.03	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-96 • **HSTL Class II – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	1.55	2.93	0.26	1.94	1.10	2.98	2.75			8.79	8.55	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-117 • **Minimum and Maximum DC Input and Output Levels**

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-118 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	VREF (typ.) (V)
1.64	1.94	Cross point	–

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-119 • **LVPECL – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.98	1.75	0.19	1.45	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-120 • **LVPECL – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	1.55	2.16	0.26	1.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-131 • Input DDR Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.76	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.94	ns
$t_{DDRISUD1}$	Data Setup for Input DDR (negedge)	0.93	ns
$t_{DDRISUD2}$	Data Setup for Input DDR (posedge)	0.84	ns
$t_{DDRIHD1}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{DDRIHD2}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear to Out Out_QR for Input DDR	1.23	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width HIGH for Input DDR	0.31	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width LOW for Input DDR	0.28	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

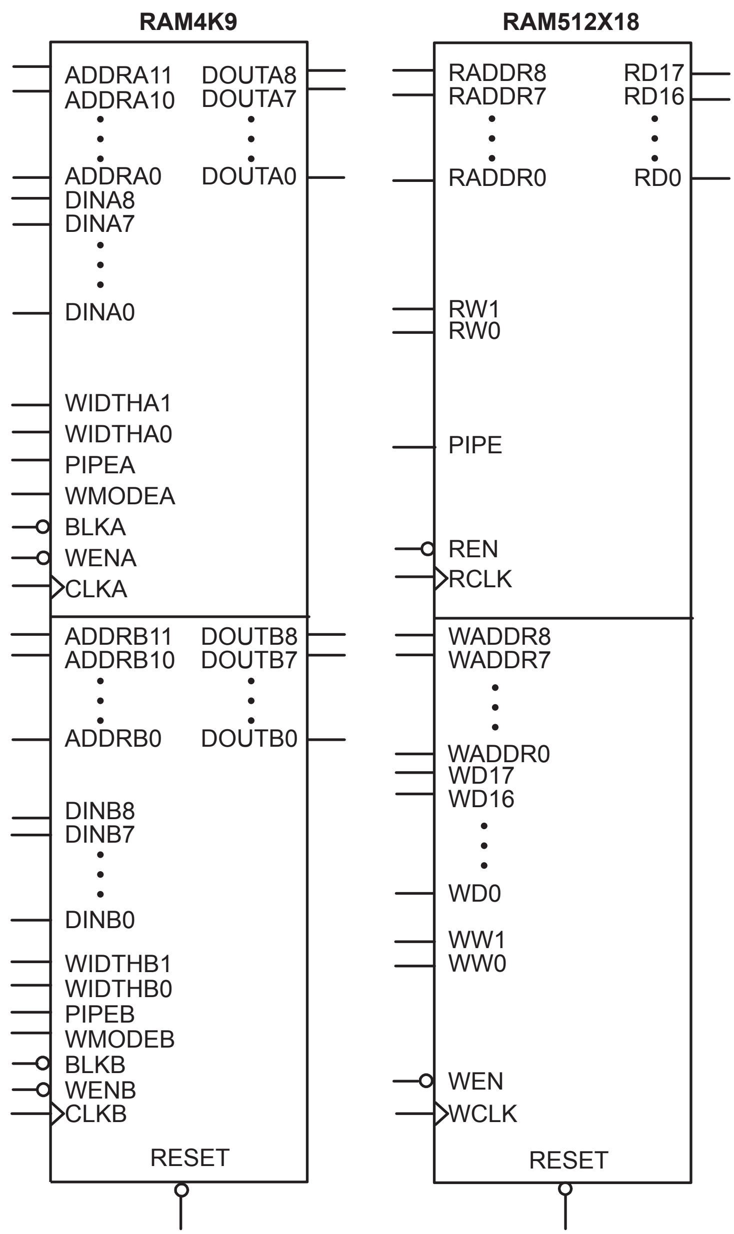

***Figure 2-41 •* RAM Models**

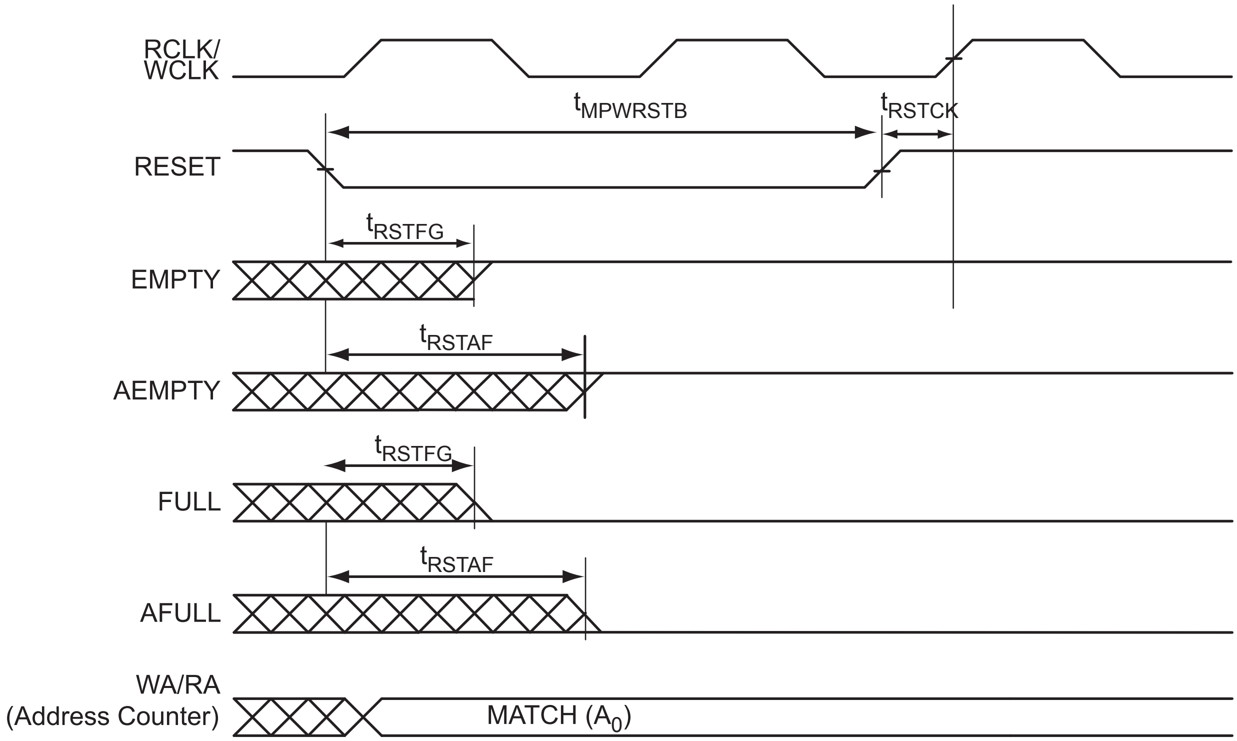

Figure 2-50 **• FIFO Reset**

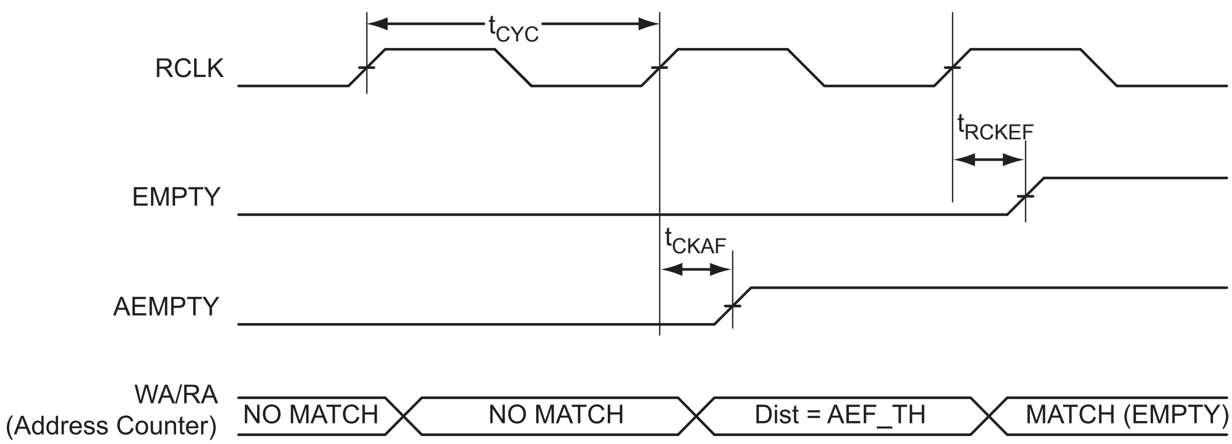

Figure 2-51 **• FIFO EMPTY Flag and AEMPTY Flag Assertion**

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-149 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.99	ns
t_{ENH}	REN, WEN Hold Time	0.16	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.76	ns
t_{DH}	Input Data (WD) Hold Time	0.25	ns
t_{CKQ1}	Clock HIGH to New Data Valid on RD (pass-through)	3.33	ns
t_{CKQ2}	Clock HIGH to New Data Valid on RD (pipelined)	1.80	ns
t_{RCKEF}	RCLK HIGH to Empty Flag Valid	3.53	ns
t_{WCKFF}	WCLK HIGH to Full Flag Valid	3.35	ns
t_{CKAF}	Clock HIGH to Almost Empty/Full Flag Valid	12.85	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	3.48	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	12.72	ns
t_{RSTBQ}	RESET LOW to Data Out LOW on RD (pass-through)	2.02	ns
	RESET LOW to Data Out LOW on RD (pipelined)	2.02	ns
$t_{REMRSTB}$	RESET Removal	0.61	ns
$t_{RECRSTB}$	RESET Recovery	3.21	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Applies to 1.2 V DC Core Voltage

Table 2-150 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.13	ns
t_{ENH}	REN, WEN Hold Time	0.31	ns
t_{BKS}	BLK Setup Time	0.47	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	1.56	ns
t_{DH}	Input Data (WD) Hold Time	0.49	ns
t_{CKQ1}	Clock HIGH to New Data Valid on RD (pass-through)	6.80	ns
t_{CKQ2}	Clock HIGH to New Data Valid on RD (pipelined)	3.62	ns
t_{RCKEF}	RCLK HIGH to Empty Flag Valid	7.23	ns
t_{WCKFF}	WCLK HIGH to Full Flag Valid	6.85	ns
t_{CKAF}	Clock HIGH to Almost Empty/Full Flag Valid	26.61	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	7.12	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	26.33	ns
t_{RSTBQ}	RESET LOW to Data Out LOW on RD (pass-through)	4.09	ns
	RESET LOW to Data Out LOW on RD (pipelined)	4.09	ns
$t_{REMRSTB}$	RESET Removal	1.23	ns
$t_{RECRSTB}$	RESET Recovery	6.58	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

FG896	
Pin Number	AGLE3000 Function
D30	GBA2/IO82PPB2V0
E1	GND
E2	IO303NPB7V3
E3	VCCIB7
E4	IO305PPB7V3
E5	VCC
E6	GAC0/IO02NDB0V0
E7	VCCIB0
E8	IO06PPB0V0
E9	IO24NDB0V2
E10	IO24PDB0V2
E11	IO13NDB0V1
E12	IO13PDB0V1
E13	IO34NDB0V4
E14	IO34PDB0V4
E15	IO40NDB0V4
E16	IO49NDB1V1
E17	IO49PDB1V1
E18	IO50PDB1V1
E19	IO58PDB1V2
E20	IO60NDB1V2
E21	IO77PDB1V4
E22	IO68NDB1V3
E23	IO68PDB1V3
E24	VCCIB1
E25	IO74PDB1V4
E26	VCC
E27	GBB1/IO80PPB1V4
E28	VCCIB2
E29	IO82NPB2V0
E30	GND
F1	IO296PPB7V2
F2	VCC
F3	IO306PDB7V4
F4	IO297PDB7V2

FG896	
Pin Number	AGLE3000 Function
F5	VMV7
F5	VMV7
F6	GND
F7	GNDQ
F8	IO12NDB0V1
F9	IO12PDB0V1
F10	IO10PDB0V1
F11	IO16PDB0V1
F12	IO22NDB0V2
F13	IO30NDB0V3
F14	IO30PDB0V3
F15	IO36PDB0V4
F16	IO48NDB1V0
F17	IO48PDB1V0
F18	IO50NDB1V1
F19	IO58NDB1V2
F20	IO60PDB1V2
F21	IO77NDB1V4
F22	IO72NDB1V3
F23	IO72PDB1V3
F24	GNDQ
F25	GND
F26	VMV2
F26	VMV2
F27	IO86PDB2V0
F28	IO92PDB2V1
F29	VCC
F30	IO100NPB2V2
G1	GND
G2	IO296NPB7V2
G3	IO306NDB7V4
G4	IO297NDB7V2
G5	VCCIB7
G6	GNDQ
G6	GNDQ

FG896	
Pin Number	AGLE3000 Function
G7	VCC
G8	VMV0
G9	VCCIB0
G10	IO10NDB0V1
G11	IO16NDB0V1
G12	IO22PDB0V2
G13	IO26PPB0V3
G14	IO38NPB0V4
G15	IO36NDB0V4
G16	IO46NDB1V0
G17	IO46PDB1V0
G18	IO56NDB1V1
G19	IO56PDB1V1
G20	IO66NDB1V3
G21	IO66PDB1V3
G22	VCCIB1
G23	VMV1
G24	VCC
G25	GNDQ
G25	GNDQ
G26	VCCIB2
G27	IO86NDB2V0
G28	IO92NDB2V1
G29	IO100PPB2V2
G30	GND
H1	IO294PDB7V2
H2	IO294NDB7V2
H3	IO300NDB7V3
H4	IO300PDB7V3
H5	IO295PDB7V2
H6	IO299PDB7V3
H7	VCOMPLA
H8	GND
H9	IO08NDB0V0
H10	IO08PDB0V0

Revision	Changes	Page
Revision 10 (April 2012)	In Table 2-2 • Recommended Operating Conditions 1, VPUMP programming voltage for operation was changed from "0 to 3.45 V" to "0 to 3.6 V" (SAR 32256). Values for VCCPLL at 1.2–1.5 V DC core supply voltage were changed from "1.14 to 1.26 V" to "1.14 to 1.575 V" (SAR 34701).	2-2
	The tables in the "Quiescent Supply Current" section were updated with revised notes on IDD. Table 2-8 • Power Supply State per Mode is new (SARs 34745, 36949).	2-7
	t_{DOUT} was corrected to t_{DIN} in Figure 2-4 • Input Buffer Timing Model and Delays (example) (SAR 37105).	2-17
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 and Table 2-30 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33855). Values were also added for 1.2 V LVCMOS and 1.2 V LVCMOS Wide Range.	2-28, 2-30
	The formulas in the table notes for Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34753).	2-29
	IOSH and IOSL values were added to 3.3 V LVCMOS Wide Range Table 2-40 • Minimum and Maximum DC Input and Output Levels, 1.2 V LVCMOS Table 2-64 • Minimum and Maximum DC Input and Output Levels, and 1.2 V LVCMOS Wide Range Table 2-68 • Minimum and Maximum DC Input and Output Levels (SAR 33855).	2-35, 2-47, 2-48
	Figure 2-48 • FIFO Read and Figure 2-49 • FIFO Write have been added (SAR 34844).	2-103
	Values for $F_{DDRIMAX}$ and F_{DDOMAX} were added to the tables in the Input DDR "Timing Characteristics" section and Output DDR "Timing Characteristics" section (SAR 34802).	2-77,2-81
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36952).	2-89
Revision 9 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34665).	I, 1-2
	The Y security option and Licensed DPA Logo were added to the "IGLOOe Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34725).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34685).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34696).	1-7
	Values for VCCPLL at 1.5 V DC core supply voltage were changed from "1.4 to 1.6 V" to "1.425 to 1.575 V" in Table 2-2 • Recommended Operating Conditions 1 (SAR 32292).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—PCLOCK" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *IGLOOe FPGA Fabric User's Guide* (SAR 34731).	2-13